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APPLICANT

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2812

U.S. PATENT DOCUMENTS

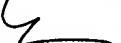

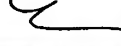

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FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY/NAME	CLASS	SUB CLASS	TRANSLATION YES NO

OTHER DOCUMENTS

	Article entitled, "Selectivity to Silicon Nitride in Chemical Vapor Deposition of Titanium Silicide", by Maa et al., published in J. Vac. Sci. Technol. B 17(5), Sep/Oct 1999, pp 2243-2247
	Article entitled, "Effects on Selective CVD of TITanium Disilicide by Substrate Doping and Selective Silicon Deposition", by Maa et al., published in Mat. Res. Soc. Symp. Proc. Vol. 564, pp. 85-89
	Article entitled, "Prevention of Corner Voiding in Selective CVD Deposition of Titanium Silicide on SOI Device", by Maa et al., published in Mat. Res. Soc. Symp. Proc. Vol. 564, pp 29-34
	Article entitled, "Selective Deposition of TiSi ₂ on Ultra-Thin Silicon-On-Insulator (SOI) Wafers", by Maa et al., published in Thin Solid Films 332(1998) pp. 412-417

EXAMINER

DATE CONSIDERED _____

2/28/03